Ref #	Hits	Search Query	DBs	Default Operato r	Plural s	Time Stamp
L1	825	power adj transistor same base same saturation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 10:14
L2	70	power adj transistor same base same saturation and "257"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 10:20
L3	32	power adj transistor same base same saturation and "257"/\$.ccls. and vertical	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ОИ	2006/08/30
L4	24	power adj transistor same base same saturation and "257"/\$.ccls. and vertical	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 10:33
L5	0	power adj transistor same base same saturation same first adj region and "257"/\$.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 10:33
L6	21	power adj transistor same base same saturation same base with region and "257"/\$.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 12:47
L7	1	current adj dencity and "257"/\$.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 13:47
L8	777	257/362,363.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 13:48
L9	270	8 and esd	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 13:49

L10	39	esd and first adj region with base	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 13:50
L11	27	esd and first adj region with base same second adj region	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 13:50
L12	24	esd and first adj region with base with second adj region	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 13:52
L13	25	esd and first adj region with base same second adj region with base	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 13:52
L14	9	13 and 8	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 16:44
L15	0	<pre>(p adj well p\$well) with seconf near (p\$layer p\$region)</pre>	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 16:46
L16	3294	second near (p\$layer p\$region)	USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2006/08/30 16:47
L17	119	second near (p\$layer p\$region) with base	USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ОИ	2006/08/30 16:48
L18	0	second near (p\$layer p\$region) with base near (p\$type)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ОИ	2006/08/30 16:48
L19	0	second near (p\$layer p\$region) with base near (p\$type)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 16:49

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L20	0	second near (n\$layer n\$region) with base near (n\$type)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 16:49
L21	1	second near (n\$layer n\$region) with n\$base	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30
L22	1	second near (n\$layer n\$region) with n\$base and second near (n\$layer n\$region) and n\$base	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/30 17:14
L23	68	(esd and transistor and zener and first near region and second near region)	US-PGPUB	OR	ON	2006/08/30 17:15
L24	5	(esd and transistor and zener and first near region and second near region).clm.	US-PGPUB	OR	ON	2006/08/30 17:15
s1	2	"20050207077"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 11:54
S6	3231	"257"/\$.ccls. and esd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 11:55
s7	398	"257"/\$.ccls. and esd and zener	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 11:57
S8	5	"257"/\$.ccls. and esd and zener and region and redistribut\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 11:59

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S9	5	"257"/\$.ccls. and esd and zener and redistribut\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 12:00
S10	3	"257"/\$.ccls. and esd and zener and redistribut\$4	USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/08/29 12:16
s11	0	"257"/\$.ccls. and bpj and zener and redistribut\$4	USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/08/29 12:17
S12	0	"257"/\$.ccls. and bypolar and zener and redistribut\$4	USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/08/29 12:18
S13	33	"257"/\$.ccls. and bipolar and zener and redistribut\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 12:19
S14	24	"257"/\$.ccls. and bipolar and zener and redistribut\$4	USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 12:19
S15	10	"257"/\$.ccls. and bipolar same zener and redistribut\$4	USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 12:20
S16	14	"257"/\$.ccls. and base same zener and redistribut\$4	USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 12:21

S17	556	"257"/\$.ccls. and base same zener same transistor	USPAT; USOCR; FPRS; EPO; JPO; DERWENT;	OR	ON	2006/08/29 12:22
s18	369	"257"/\$.ccls. and base with zener same transistor	IBM_TDB USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM TDB	OR	ON	2006/08/29 12:39
S19	93	"257"/\$.ccls. and base with zener same transistor and (esd discharge)	USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 14:28
S20	2	"6365462".pn.	USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 14:42
S21	9949	bipolar adj transistor same base with region	USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ОИ	2006/08/29 14:43
S22	356	bipolar adj transistor same base with region and esd	USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 14:44
S23	3546	bipolar adj transistor same base with region same surface	USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 14:44
S24	2402	bipolar adj transistor same base with region with surface	USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 14:44

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\$25	178	bipolar adj transistor same base with region with surface with current	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 14:46
S26	0	bipolar adj transistor same base with region with surface with current with (distribute redistribute)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 14:46
s27	2	bipolar adj transistor same base with region with current with (distribute redistribute)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ОИ	2006/08/29 15:19
S28	0	bipolar adj transistor same base with depth with current with (distribute redistribute)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:18
S29	0	transistor same base with depth with current with (distribute redistribute)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ОИ	2006/08/29 15:18
\$30	2385	transistor same base with depth	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ОИ	2006/08/29 15:19
S31	3318	transistor same base with (depth deep)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ОИ	2006/08/29 15:19

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S32	0	bipolar adj transistor same base with region with (depth deep) with (distribute redistribute)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:19
\$33	1	bipolar adj transistor same base with region with (depth deep) same (distribute redistribute)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ОИ	2006/08/29 15:21
S34	163	bipolar adj transistor same base with region with (depth deep) same current	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:23
\$35	122	bipolar adj transistor same base near3 region with (depth deep) same current	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:57
\$36	260	base near3 region with (depth deep) same current same surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:58
s37	0	base near3 region with (depth deep) same current near2 from near surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:59
S38	0	base near3 region with (depth deep) same current near2 from near2 surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:59

S39	0	base near3 region with (depth deep) same (redirecte redistribut\$3) near2 from near2 surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 16:00
S40	0	base near3 region with (depth deep) same (redirect\$3 redistribut\$3) with from near2 surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 16:01
S41	0	base near3 region with (depth deep) same (redirect\$3 redistribut\$3) with from with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 16:01
S42	6	base near3 region with (depth deep) same (redirect\$3 redistribut\$3) with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 16:12
S43	0	base near3 first adj region with (depth deep) same (redirect\$3 redistribut\$3) with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 16:13
S44	0	base with first adj region with (depth deep) same (redirect\$3 redistribut\$3) with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ОИ	2006/08/29 16:13
S45	2	base with first adj region same (redirect\$3 redistribut\$3) with surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 16:13